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N-Channel 60 V (D-S) MOSFET



PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}$ (m Ω)	I _D (A) ^a	
60	6.9 at V _{GS} = 10 V	70	
	9.5 at V _{GS} = 4.5 V	60	

TO-252

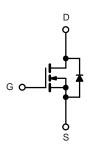
G D S

FEATURES

- 175 °C Junction Temperature
- DT-Trench Power MOSFET

APPLICATIONS

• DC/DC converters



N-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C	L	70		
	T _C = 100 °C	l _D	65 ^a		
Pulsed Drain Current		I _{DM}	280	А	
Continuous Source Current (Diode Conduction)		Is	70 ^a		
Avalanche Current		I _{AS}	69		
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	375	mJ	
Manifesture Device Discination	T _C = 25 °C	В	186	W	
Maximum Power Dissipation	T _A = 25 °C	P _D	3.5 ^b , 8.8 ^{b, c}		
Operating Junction and Storage Temperature Range	•	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manianura lunation to Ambianta	t ≤ 10 sec	R _{thJA}	13	18	°C/W
Maximum Junction-to-Ambient ^a	Steady State		35	50	
Maximum Junction-to-Case	ction-to-Case		0.81	1.1	

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. $t \le 10 \text{ s}$.

Rev. 1. 0





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SPECIFICATIONS (T _J = 25 Parameter	Symbol	Test Conditions	Min.	T 2	Max.	Unit
	Symbol	rest conditions	IVIIII.	Typ. ^a	IVIAA.	Offic
Static Paris Common Paris I de la Vallence	1 1/	V 0.V.L 250A	00			
Drain-Source Breakdown Voltage	V _{DS}					V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1		3	<u> </u>
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current		$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
	I _{DSS}	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			50	
		$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 \text{ °C}$			250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	100			Α
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A		6.9	7.9	mΩ
		V _{GS} = 4.5 V, I _D = 10 A		9.5	11.5	
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		65		S
Dynamic	-			<u>'</u>		
Input Capacitance	C _{iss}			1550		pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		360		
Reverse Transfer Capacitance	C _{rss}			115		
Total Gate Charge ^c	Q_g			67	90	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$		20		nC
Gate-Drain Charge ^c	Q_{gd}			15.5		
Turn-On Delay Time ^c	t _{d(on)}			11		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, R_L = 0.6 \Omega$ $I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		16		ns
Turn-Off Delay Time ^c	t _{d(off)}			35		
Fall Time ^c	t _f			20		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)				
Pulsed Current	I _{SM}				280	Α
Diode Forward Voltage	V _{SD}	I _F = 10 A, V _{GS} = 0 V		1	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs		45	100	ns

Notes:

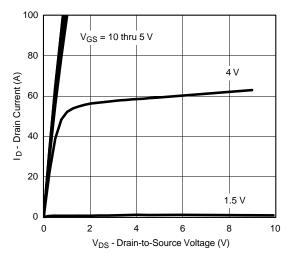
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

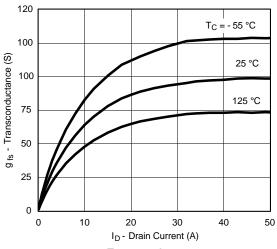




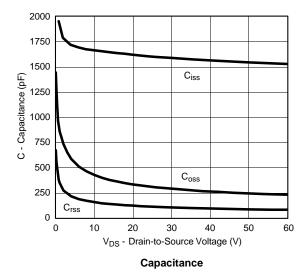
TYPICAL CHARACTERISTICS (25 °C unless noted)

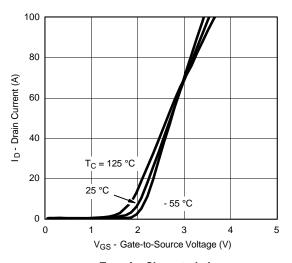


Output Characteristics

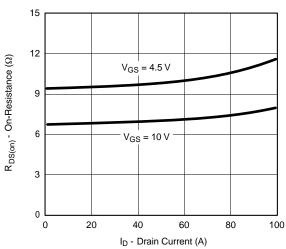


Transconductance

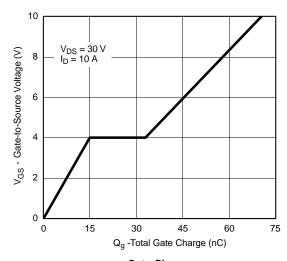




Transfer Characteristics



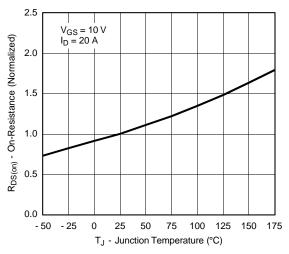
On-Resistance vs. Drain Current



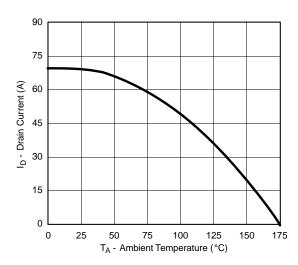
Gate Charge



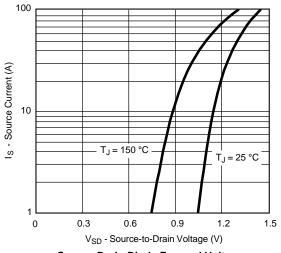
TYPICAL CHARACTERISTICS (25 °C unless noted)



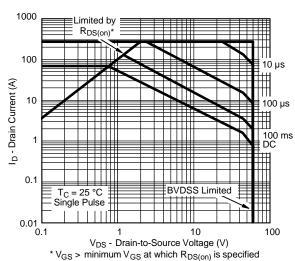
On-Resistance vs. Junction Temperature



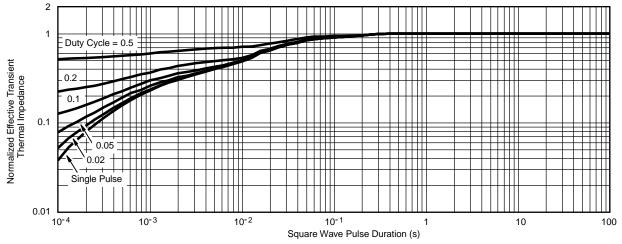
Maximum Drain Current vs. Ambient Temperature



Source-Drain Diode Forward Voltage



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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